

TCU12UYG-S



❖ Features:

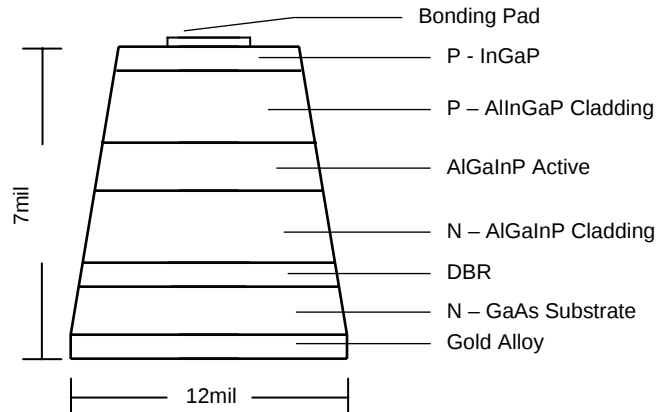
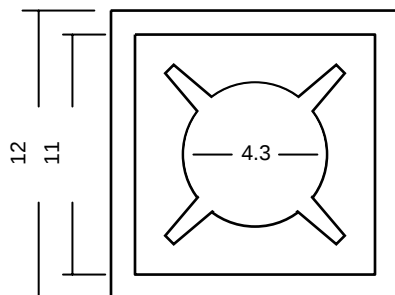
- AlInGaP/GaAs LED Chips
- MOVPE Process Wafer
- MQW and DBR
- Roughen Surface

❖

Typical Applications

- Indoor/Outdoor Applications

❖ Outline Dimensions:



❖ Physical Structure:

Chip dimensions		Chip size	12 mil x 12 mil	305 μm x 305 μm
		Thickness	7 mil	178 μm
		Emission area	11 mil	279 μm
		Bonding pad	4.3 mil	109 μm
Electrode	Top	P (anode)	Gold alloy	
	Backside	N (cathode)	Gold alloy	

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$		2.00	2.40	V
Wavelength	λ_D	$I_F = 20\text{mA}$	572	575	578	
Spectral width at half height	$\Delta\lambda$	$I_F = 20\text{mA}$	-	15	-	nm
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5	-	-	V
Luminous Intensity	I_v	A1	20	-	-	mcd
		B1	30	-	-	
		C1	40	-	-	

❖ Note. Also available:

Chip size		Min. Luminous Intensity
mils	μm	mcd
9	229 x 229	20
9	229 x 229	30
9	229 x 229	40

YELLOW-GREEN